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MOS FET

FK3F03080L

Panasonic

FK3F03080L Silicon N-channel MOSFET

For switching circuits

■ Features

Low drive voltage : 2.5 V driveHalogen-free / RoHS compliant

(EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : X8

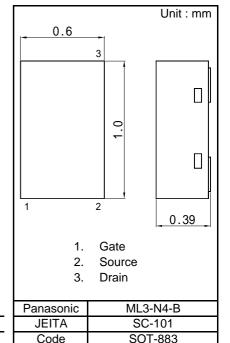
Packaging

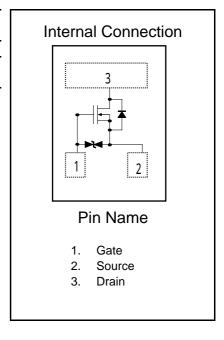
Embossed type (Thermo-compression sealing): 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

	Parameter	Symbol	Rating	Unit	
	Drain to Source Voltage	VDS	30	V	
•	Gate to Source Voltage	VGS	±20	V	
	Drain Current	ID	100	mA	
	Drain Current (Pulsed) *1	IDp	200	IIIA	
	Total Power Dissipation	PD	100	mW	
	Channel Temperature	Tch	150	°C	
	Storage Temperature Range	Tstg	-55 to +150)	

Note *1 Pulse test: Ensure that the channel temperature does not exceed 150 °C





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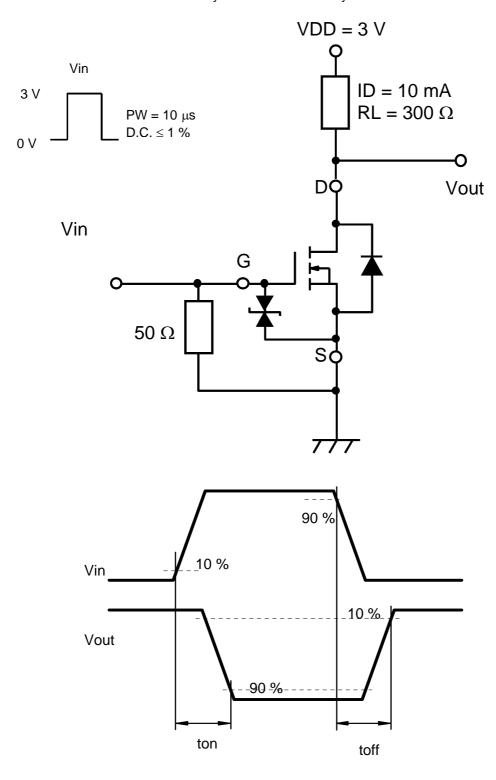
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			1	μΑ
Gate-source Leakage Current	IGSS	$VGS = \pm 16 \text{ V}, VDS = 0 \text{ V}$			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = $6.9 \mu A$, VDS = $10 V$	0.6		2.0	V
Drain-source On-state Resistance	RDS(on)1	ID = 10 mA, VGS = 2.5 V		4.0	12	Ω
	RDS(on)2	ID = 100 mA, VGS = 4.5 V		1.0	1.4	
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V		11		pF
Output Capacitance	Coss	f = 1 MHz		6.8		
Reverse Transfer Capacitance	Crss	1 = 1 1011 12		3.5		
Turn-on Delay Time ^{*1}	ton	VDD = 3 V, VGS = 0 to 3 V ID = 10 mA, RL = 300 Ω		20		ns
Turn-off Delay Time ^{*1}	toff	VDD = 3 V, VGS = 3 to 0 V ID = 10 mA, RL = 300 Ω		100		ns

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

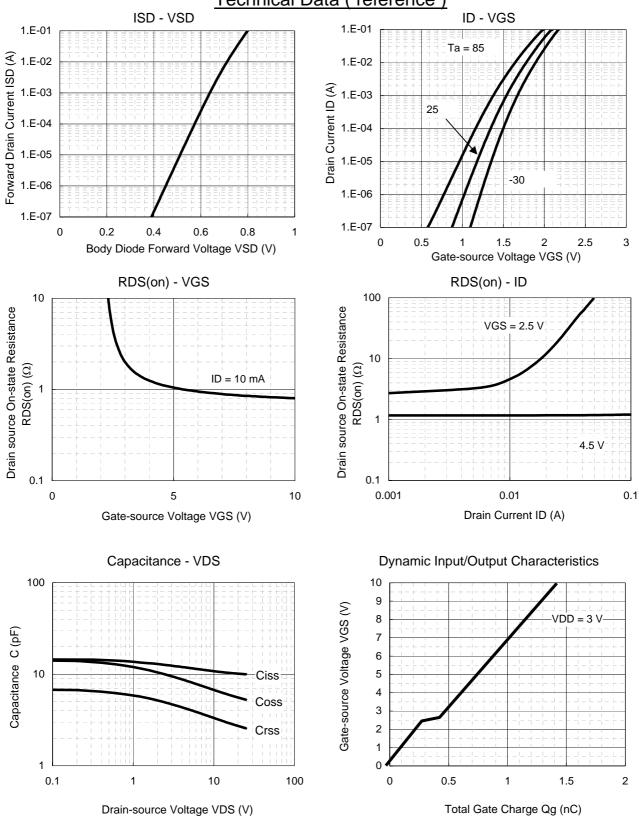
2. *1 Measurement circuit for Turn-on Delay Time / Turn-off Delay Time

*1 Measurement circuit for Turn-on Delay Time / Turn-off Delay Time



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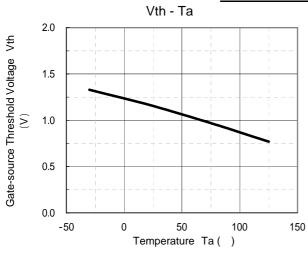


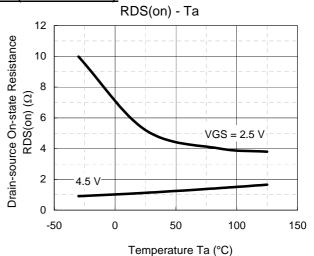
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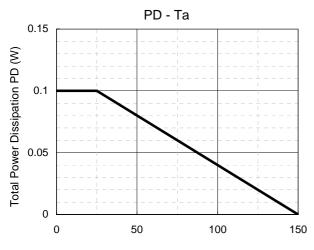
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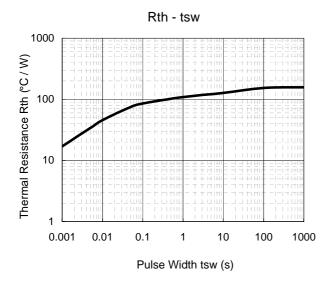
Technical Data (reference)



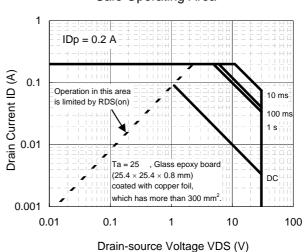




Temperature Ta (°C)



Safe Operating Area



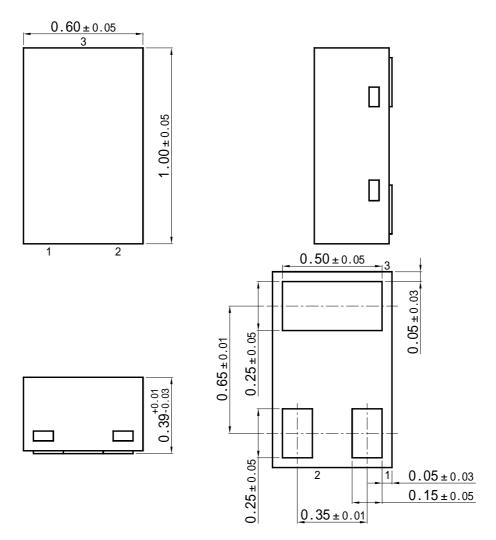
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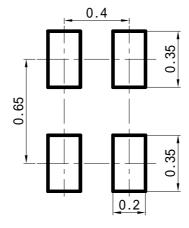
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ML3-N4-B

Unit: mm



■ Land Pattern (Reference) (Unit : mm)



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